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TN6727A



PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1A. Sourced from Process 77. See TN6726A for characteristics.

Absolute Maximum Ratings*

T_{A = 25°C unless otherwise noted}

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current - Continuous	1.5	Α
T _{J, ⊺stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

Thermal Characteristics ___ T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN6727A	
P _D	Total Device Dissipation Derate above 25°C	1 8	W mW/°C
R ₀ JC	Thermal Resistance, Junction to Case	50	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	125	°C/W

¹⁾ These ratings are based on a maximum junction temperature of 150°C.

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

PNP General Purpose Amplifier

(continued)

Electrical Characteristics

 $T_{A\,=\,25^{\circ}\text{C unless otherwise noted}}$

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	40		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1 mA	50		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 1 mA	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 50 V		100	nA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5 V		100	nA
ON CHAI	RACTERISTICS*				
h _{FE}	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 1 \text{ V}$ $I_{C} = 1A, V_{CE} = 1 \text{ V}$	55 60 50	250	-
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		0.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 1 V		1.2	V
SMALL S	IGNAL CHARACTERISTICS				
C _{cb}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		30	pF
h _{fe}	Small Signal Current Gain	I _C = 50 mA,V _{CE} = 10 V, f=20MHz	2.5	25	-

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1.0%

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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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